

N-channel 60 V, 4.8 mΩ logic level MOSFET in LFPAK56 7 January 2016

Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

#### Applications 3.

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching •

#### Quick reference data 4.

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	238	W
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	3.3	4.8	mΩ
Dynamic chara	acteristics						,
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 48 V; $V_{GS}$ = 5 V; $T_j$ = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	18.1	-	nC

[1] Continuous current is limited by package.

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3.       Ordering information							
Type number	Package						
	Name	Description	Version				
BUK9Y4R8-60E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y4R8-60E	94E860

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	60	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; T <sub>j</sub> ≤ 175 °C	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	238	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[3]	-	100	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[ <u>3]</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	593	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	593	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 100 \text{ A};  \text{V}_{\text{sup}} \leq 60  \text{V};  \text{R}_{\text{GS}} = 50  \Omega; \\  \text{V}_{\text{GS}} &= 5  \text{V};  \text{T}_{\text{j(init)}} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[4][5]	-	199	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering  $\rm T_{j}$  and or  $\rm V_{GS}$ [1]
- [2]
- Continuous current is limited by package. [3]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [4]
- [5] Refer to application note AN10273 for further information.

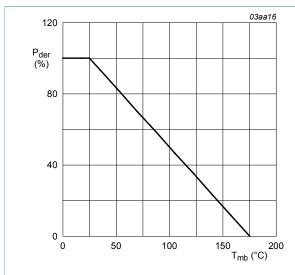
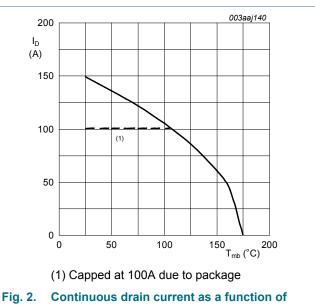
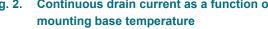


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

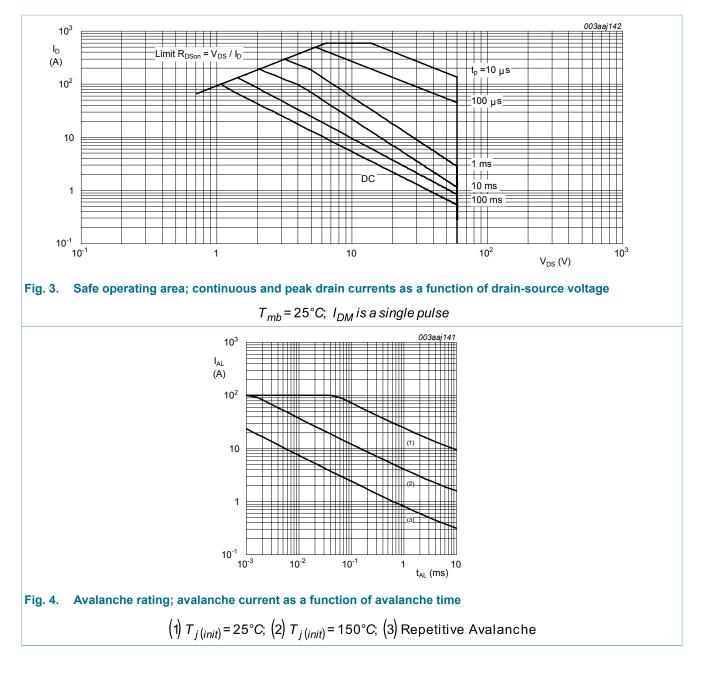
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$





 $V_{GS} \ge 5V$ 

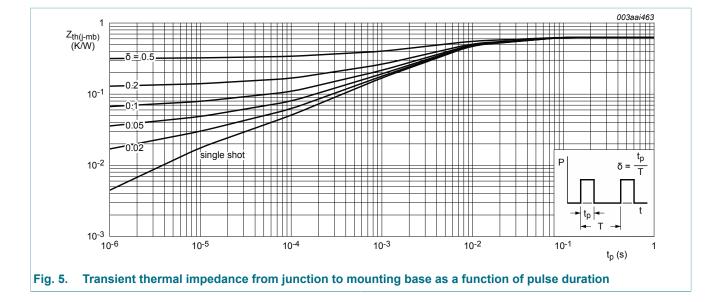
#### N-channel 60 V, 4.8 mΩ logic level MOSFET in LFPAK56



### 9. Thermal characteristics

Fable 6.       Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5		-	-	0.63	K/W	

#### N-channel 60 V, 4.8 mΩ logic level MOSFET in LFPAK56



### **10. Characteristics**

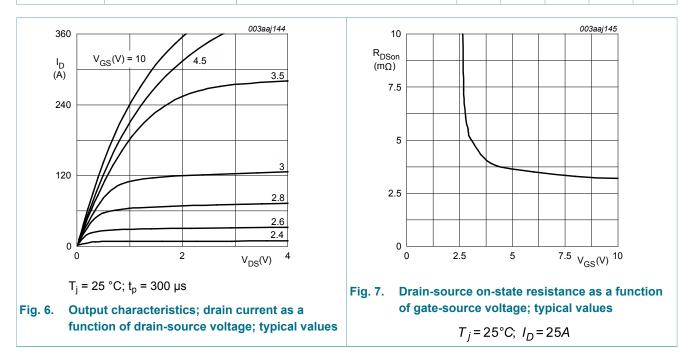
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	54	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I <sub>DSS</sub> drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.12	10	μA	
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub> g	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	3.3	4.8	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	2.9	4.1	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	10.8	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;	-	54.8	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	13.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	18.1	-	nC

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# **BUK9Y4R8-60E**

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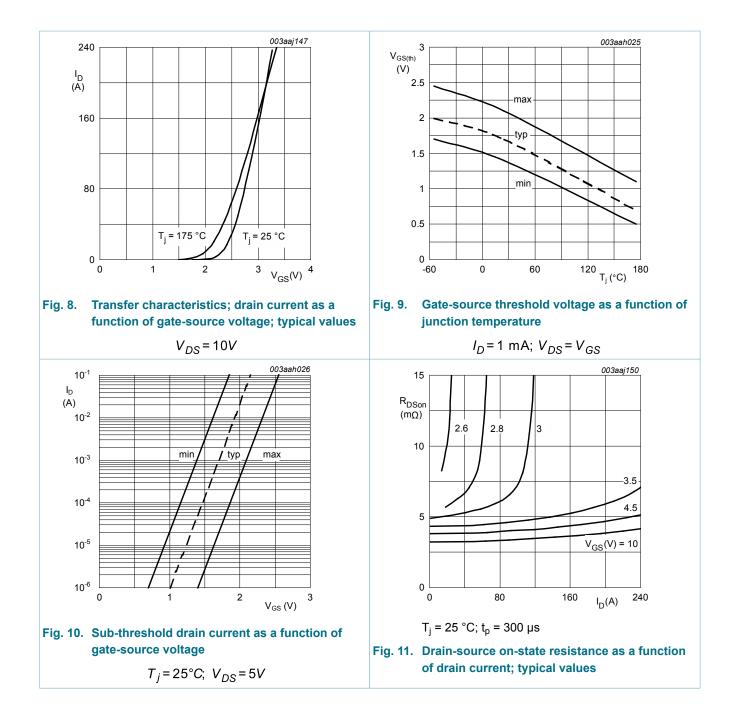
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;		-	5890	7853	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	506	607	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{1} = 45 V_{1} D_{1} = 1.0 O_{1} V_{1} = 5 V_{1}$		-	276	378	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; R <sub>L</sub> = 1.8 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C		-	28	-	ns
t <sub>r</sub>	rise time			-	53	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	80	-	ns
t <sub>f</sub>	fall time			-	47	-	ns
Source-dra	ain diode	1	II			1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	29	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C		-	28	-	nC



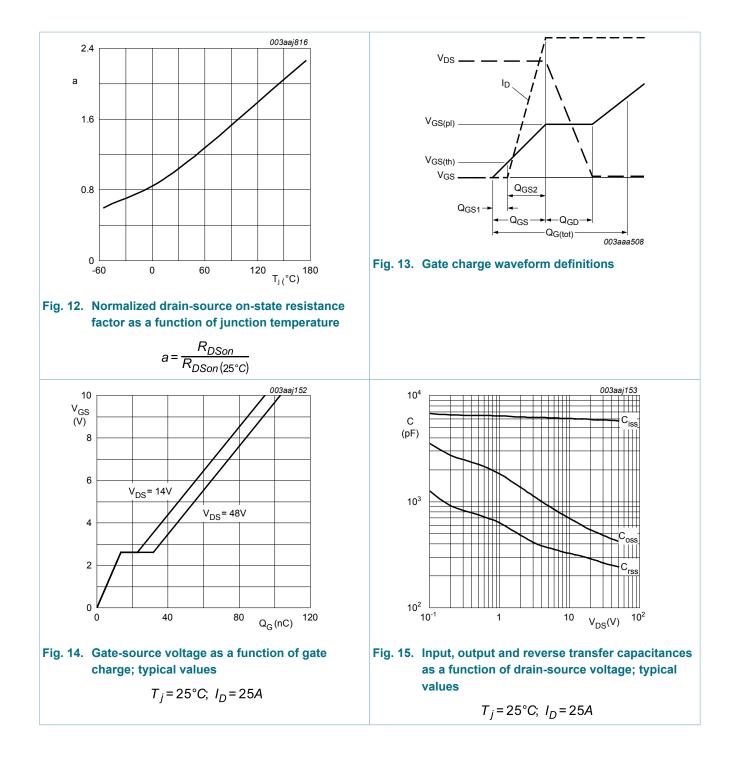
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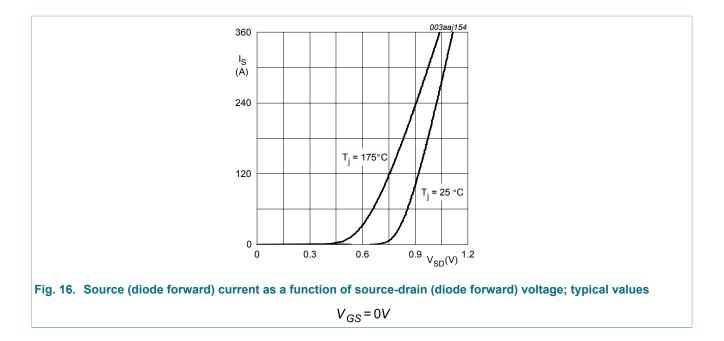


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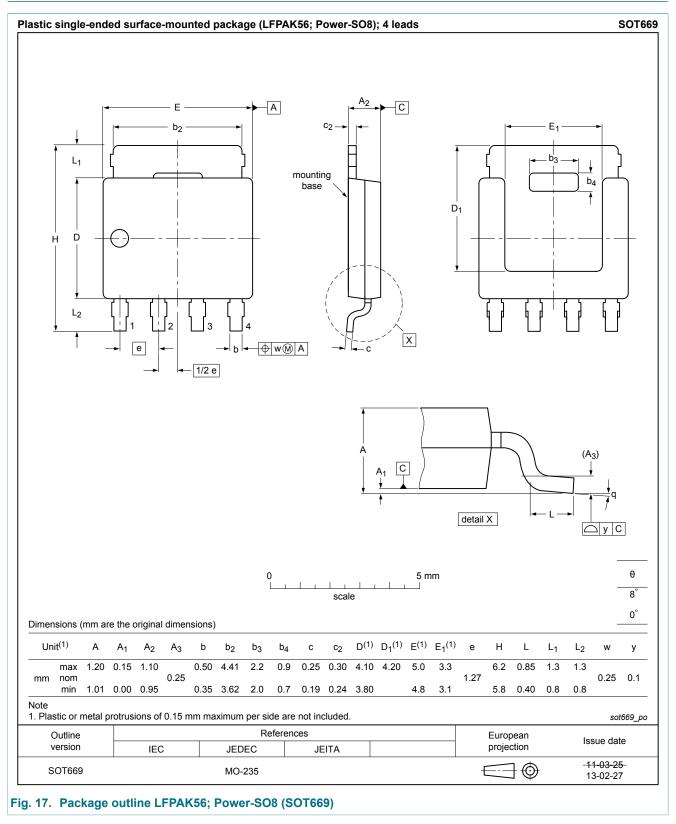
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#### N-channel 60 V, 4.8 mΩ logic level MOSFET in LFPAK56

### **11. Package outline**



BUK9Y4R8-60E

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#### N-channel 60 V, 4.8 m $\Omega$ logic level MOSFET in LFPAK56

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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